

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
-100V	36mΩ@-10V	-25A
	51mΩ@-4.5V	

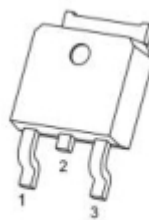
## Feature

- Fast Switching
- Low On-Resistance
- Excellent FOM

## Application

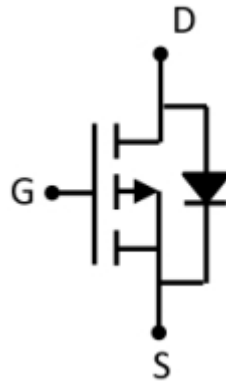
- Motor control
- Switching Regulators
- Isolated DC/DC convertor
- Alertor

## Package



TO-252(1:G 2:D 3:S)

## Circuit diagram



## Marking



**010P36G** =Device Code  
**\*\*** =Week Code

## Absolute maximum ratings

( $T_a=25^{\circ}\text{C}$  unless otherwise noted)

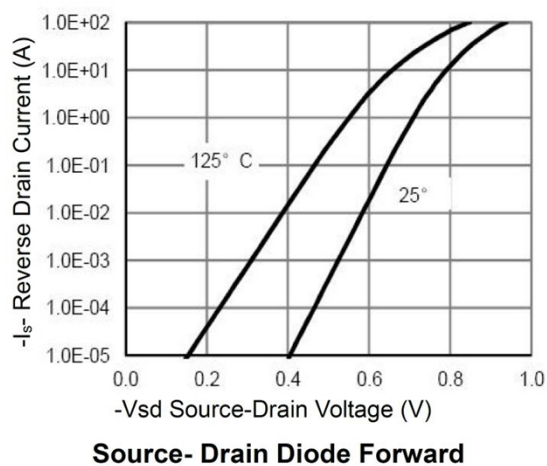
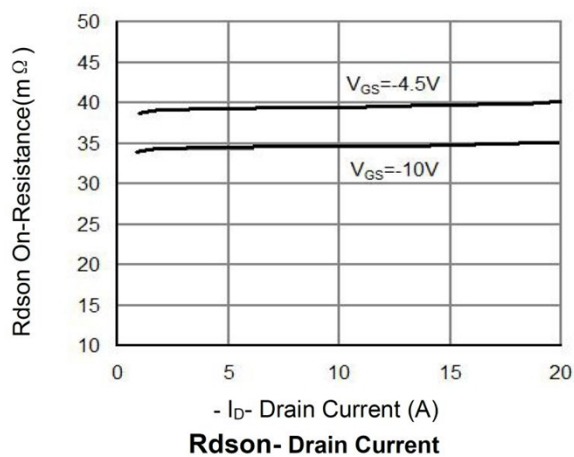
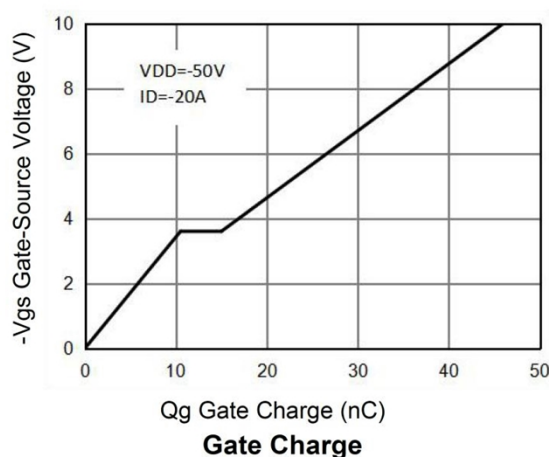
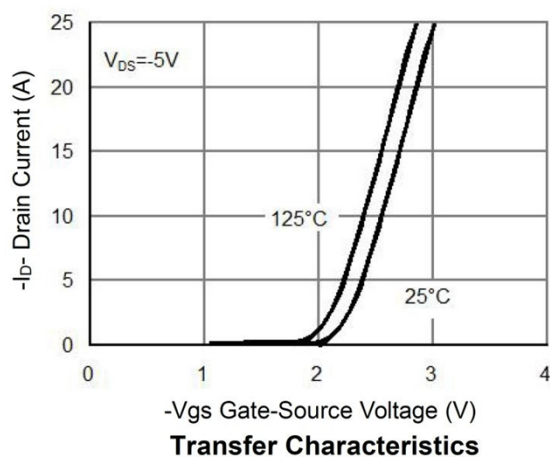
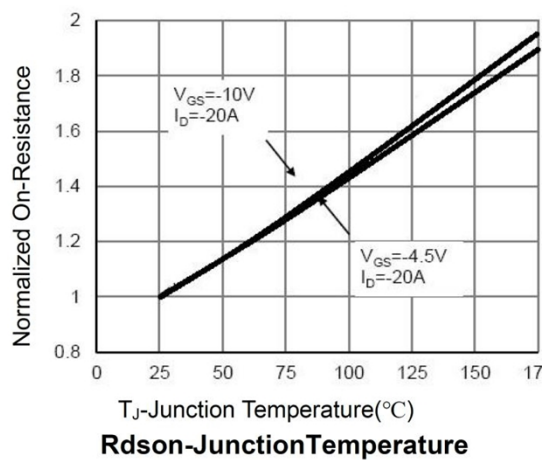
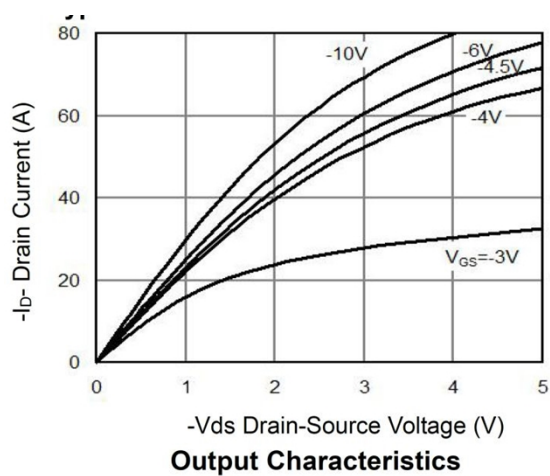
Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	-100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	-25	W
Drain Current – Pulsed <sup>1</sup>	$I_{DM}$	-100	A
Power Dissipation ( $T_c=25^{\circ}\text{C}$ )	$P_D$	120	W
Thermal Resistance Junction to Case	$R_{\theta JC}$	1.04	$^{\circ}\text{C}/\text{W}$
Storage Temperature Range	$T_{STG}$	-55~ +150	$^{\circ}\text{C}$
Operating Junction Temperature Range	$T_J$	-55~ +150	$^{\circ}\text{C}$

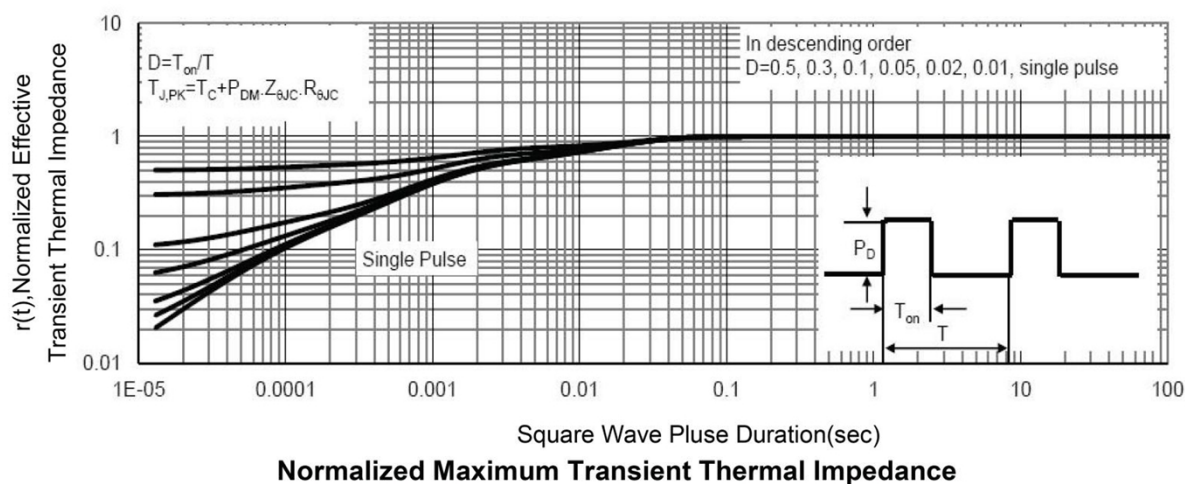
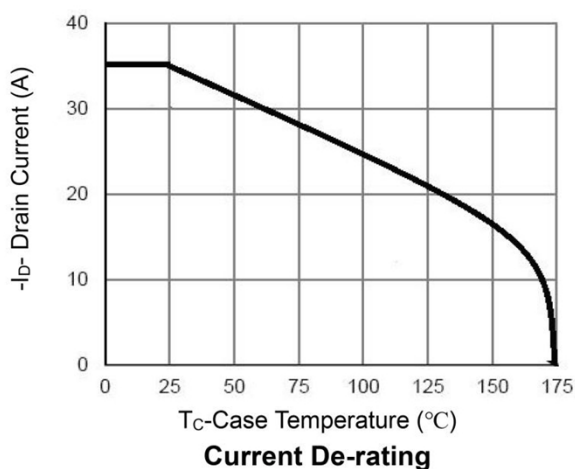
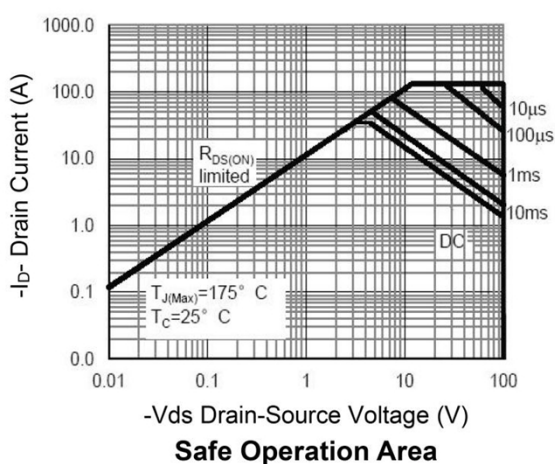
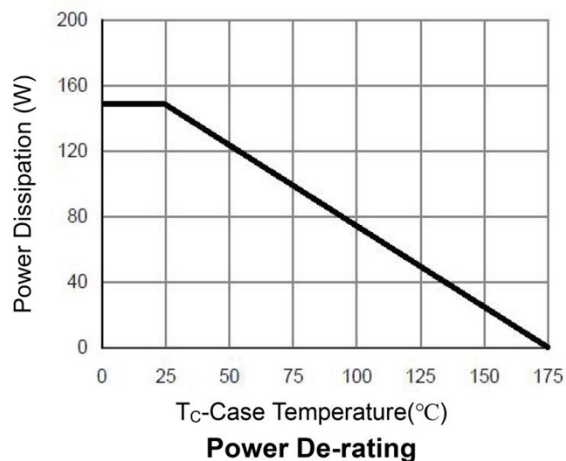
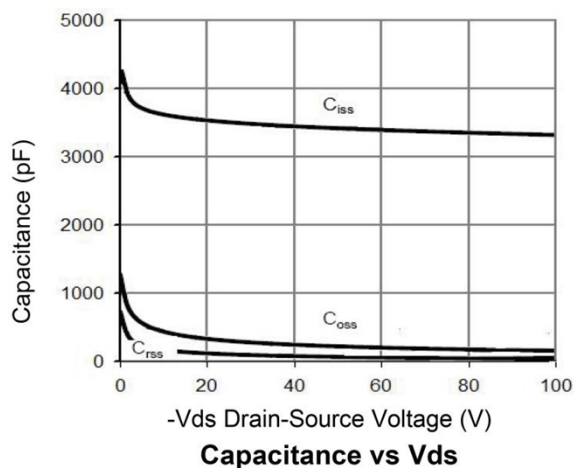
## Electrical characteristics

( $T_A=25^{\circ}\text{C}$ , unless otherwise noted)

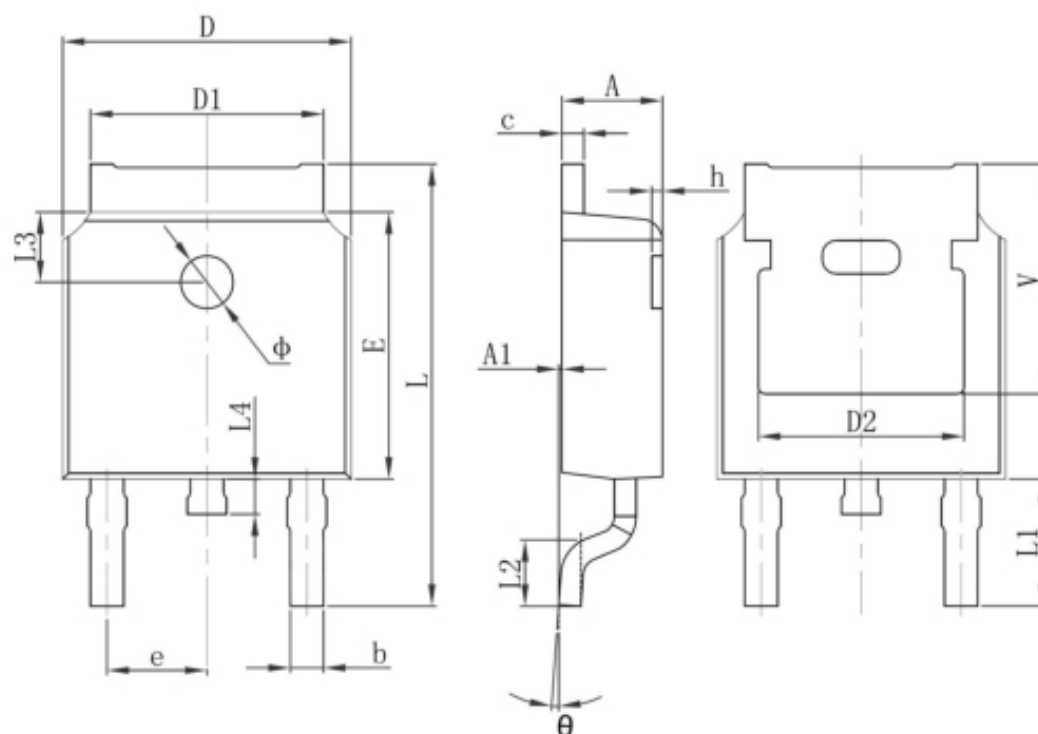
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA	-100			V
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> = -100V,V <sub>GS</sub> = 0V			-1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V , V <sub>DS</sub> =0V			±100	uA
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> = -250μA	-1	-2.2	-3	V
Static Drain-Source on-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10V, I <sub>D</sub> = -15A		36	45	mΩ
		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -10A		51	68	
Dynamic characteristics <sup>4</sup>						
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> = -10V, V <sub>DS</sub> = -50V, I <sub>D</sub> = -15A		20		nC
Gate-Source Charge	Q <sub>gS</sub>			6.1		
Gate-Drain Charge	Q <sub>gd</sub>			3.5		
Turn-On Delay Time	T <sub>d(on)</sub>	V <sub>GS</sub> = -10V, V <sub>DD</sub> = -50V, I <sub>D</sub> = -15A, R <sub>GEN</sub> =6Ω		11		nS
Rise Time	T <sub>r</sub>			56		
Turn-Off Delay Time	T <sub>d(off)</sub>			46		
Fall Time	T <sub>f</sub>			84		
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -50V,V <sub>GS</sub> =0V, f=1MHz		1415		pF
Output Capacitance	C <sub>oss</sub>			217		
Reverse Transfer Capacitance	C <sub>rss</sub>			3		
Drain-Source Diode Characteristics						
Continuous Source Current	I <sub>S</sub>	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			-30	A
Diode forward voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> = -1A			-1.2	V

## Typical Characteristics





## TO-252 Package Information



Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 REF.		0.211 REF.	